

Satoshi Shigematsu

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Proximity Gettering Design of Hydrocarbon Molecular Ion Implanted Silicon Wafers Using Dark Current Spectroscopy for CMOS Image Sensors. <i>Sensors</i> , 2019, 19, 2073.	3.8	20
2	Trapping and diffusion behaviour of hydrogen simulated with TCAD in projection range of carbon cluster implanted silicon epitaxial wafers for CMOS image sensors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, .	0.8	19
3	Hydrogen passivation for reduction of SiO ₂ /Si interface state density using hydrocarbon-molecular-ion-implanted silicon wafers. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 125502.	1.5	13
4	Proximity gettering of silicon wafers using CH ₃ O multielement molecular ion implantation technique. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 096503.	1.5	12
5	Room-temperature bonding of epitaxial layer to carbon-cluster ion-implanted silicon wafers for CMOS image sensors. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 061302.	1.5	8
6	Gettering mechanism in hydrocarbon-molecular-ion-implanted epitaxial silicon wafers revealed by three-dimensional atom imaging. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 091302.	1.5	7
7	A Review of Proximity Gettering Technology for CMOS Image Sensors Using Hydrocarbon Molecular Ion Implantation. <i>Sensors and Materials</i> , 2019, 31, 1939.	0.5	7
8	Gettering Sinks for Metallic Impurities Formed by Carbon-Cluster Ion Implantation in Epitaxial Silicon Wafers for CMOS Image Sensor. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 1200-1206.	2.1	6
9	Molecular and Atomic Hydrogen Diffusion Behavior by Reaction Kinetic Analysis in Projection Range of Hydrocarbon Molecular Ion for CMOS Image Sensors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900175.	1.8	5
10	Proximity gettering technique using CH ₃ O multielement molecular ion implantation for the reduction of the white spot defect density in CMOS image sensor. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 091002.	1.5	5
11	Influence of oxygen on copper gettering in hydrocarbon molecular ion implanted region using atom probe tomography. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2020, 478, 99-103.	1.4	4
12	Effect of hydrocarbon molecular ion size for amorphous region formation analyzed by X-ray photoelectron spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 025510.	1.5	3
13	(Invited) Proximity Gettering Design of Hydrocarbon Molecular Ion Implanted Silicon Wafers Using Direct Bonding Technique for Advanced CMOS Image Sensors: A Review. <i>ECS Transactions</i> , 2018, 86, 77-93.	0.5	2
14	Hydrogen diffusion behavior in CH ₂ P-molecular-ion-implanted silicon wafers for CMOS image sensors. <i>Materials Science in Semiconductor Processing</i> , 2022, 137, 106211.	4.0	1
15	Effect of ramping up rate on end of range defect in multielement molecular-ion (CH ₃ O)-implanted silicon wafers. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 121002.	1.5	1
16	Dissociation Kinetics of Trapped Hydrogen in High-dose Hydrocarbon-Molecular-Ion-Implanted Silicon during Rapid Thermal Annealing. <i>E-Journal of Surface Science and Nanotechnology</i> , 2022, , .	0.4	0